

FORM PTO-1449 (Modified)			Attorney Docket No.: 16301-034400US		Application No.: 09/648,395	
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)			Applicant: Michael Kwan, et al.			
			Filing Date: September 24, 2000		Group: 1765	
Reference Designation			U.S. PATENT DOCUMENTS			Page 1
Examiner Initial	Document No.	Date	Name	Class	Sub-class	Filing Date (If Appropriate)
<u>Dr</u> AA	4,468,413	08/28/84	Bachmann	427	39	
<u>Dr</u> AB	4,851,370	07/25/89	Doklan et al.	437	225	
<u>Dr</u> AC	4,872,947	10/10/89	Wang et al.	156	643	
<u>Dr</u> AD	4,892,753	01/09/90	Wang et al.	427	38	
<u>Dr</u> AE	4,894,352	01/16/90	Lane et al.	437	238	
<u>Dr</u> AF	4,960,488	10/02/90	Law et al.	156	643	
<u>Dr</u> AG	5,000,113	03/19/91	Wang et al.	118	723	
<u>Dr</u> AH	5,013,691	05/07/91	Lory et al.	437	238	
<u>Dr</u> AI	5,089,442	02/18/92	Olmer	432	235	
<u>Dr</u> AJ	5,156,881	10/20/92	Okano et al.	424	572	
<u>Dr</u> AK	5,215,787	06/01/93	Homma	427	248.1	
<u>Dr</u> AL	5,271,972	12/21/93	Kwok et al.	427	579	
<u>Dr</u> AM	5,275,977	01/04/94	Otsubo et al.	437	235	
<u>Dr</u> AN	5,279,865	01/18/94	Chebi et al.	427	574	
<u>Dr</u> AO	5,288,518	02/22/94	Homma	427	255.1	
<u>Dr</u> AP	5,302,233	04/12/94	Kim et al.	156	636	
<u>Dr</u> AQ	5,314,724	05/24/94	Tsukune et al.	427	489	
<u>Dr</u> AR	5,319,247	06/07/94	Matsuura	257	760	
<u>Dr</u> AS	5,334,552	08/02/94	Homma	437	195	
<u>Dr</u> AT	5,385,763	01/31/95	Okano et al.	427	572	
<u>Dr</u> AU	5,399,529	03/21/95	Homma	437	195	
<u>Dr</u> AV	5,413,967	05/09/95	Matsuda et al.	437	235	
<u>Dr</u> AW	5,416,048	05/16/95	Blalock et al.	437	228	
<u>Dr</u> AX	5,420,075	05/30/95	Homma et al.	437	195	
<u>Dr</u> AY	5,429,995	07/04/95	Nishiyama et al.	437	238	
<u>Dr</u> AZ	5,474,589	12/12/95	Ohga et al.	65	397	
<u>Dr</u> BA	5,563,105	10/08/96	Dobuzinsky et al.	437	240	
<u>Dr</u> BB	5,571,576	11/05/96	Qian et al.	427	574	
<u>Dr</u> BC	5,599,740	02/04/97	Jang et al.	437	190	
<u>Dr</u> BD	5,648,175	07/15/97	Russell et al.	428	472.3	
<u>Dr</u> BE	5,661,093	08/26/97	Ravi et al.	438	763	
<u>Dr</u> BF	5,719,085	02/17/98	Moon et al.	438	424	
<u>Dr</u> BG	5,850,105	12/15/98	Dawson et al.	257	758	
<u>Dr</u> BH	5,872,052	02/16/99	Iyer	438	622	
<u>Dr</u> BI	5,937,323	08/10/99	Orczyk et al.	438	624	
<u>Dr</u> BJ	5,939,831	08/17/99	Fong et al.	315	111.21	

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<u>JK</u> BK	5,944,902	08/31/99	Redeker et al.	118	723 AN	
<u>JK</u> BL	6,136,685	10/24/00	Narwankar et al.	438	624	
<u>JK</u> BM	08/344,283	11/22/94	Mizuno			
<u>JK</u> BN	08/584,042	01/06/96	Rana et al.			
<u>JK</u> BO	09/400,338	09/21/99	Xia et al.			
FOREIGN PATENT DOCUMENTS						
	Document No.	Date	Country	Class	Sub-class	Translation (Yes/No)
<u>JK</u> BP	WO 92/20833	11/26/92	PCT	C23C	16/00	Yes
<u>JK</u> BQ	4-341568	11/27/92	JP	C23 C16	40	No (abstract only)
<u>JK</u> BR	4-239750	08/27/92	JP	H01 L21	90	No (abstract only)
<u>JK</u> BS	J6 1276-977-A	12/06/86	JP	C23 C16	50	No (abstract only)
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)						
<u>JK</u> BT	Usami et al. "Low Dielectric Constant Interlayer Using Fluorine-Doped Silicon Oxide", Jpn. J. Appl. Phys. Vol. 33, January 1994. pp. 408-412.					
<u>JK</u> BU	Lee et al. "Dielectric Planarization Techniques For Narrow Pitch Multilevel Interconnects", VMIC Conference. June 1987. pp. 85-92.					
<u>JK</u> BV	Abraham, "Reactive Facet Tapering of Plasma Oxide For Multilevel Interconnect Applications", VMIC Conference. June 1987. pp. 115-121.					
<u>JK</u> BW	Shapiro et al. "Dual Frequency Plasma CVD Fluorosilicate Glass: Water Absorption And Stability", DUMIC Conference. February 1995. pp. 118-123.					
<u>JK</u> BX	Matsuda et al. "Dual Frequency Plasma CVD Fluorosilicate Glass: Deposition for 0.25 um Interlevel Dielectrics", DUMIC Conference. February 1995. pp. 22-28.					
<u>JK</u> BY	Qian et al. "High Density Plasma Deposition and Deep Submicron Gap Fill with Low Dielectric Constant SiOF Films", California. DUMIC Conference. February 1995. pp. 50-56.					
<u>JK</u> BZ	Fukada et al. "Preparation of SiOF Films with Low Dielectric Constant By ECR Plasma CVD", Japan. DUMIC Conference. February 1995. pp. 43-49.					
<u>JK</u> CA	Laxman, "Low e Dielectrics: CVD Fluorinated Silicon Dioxides", Semiconductor International. May 1995. pp. 71-74.					
<u>JK</u> CB	Hayasaka et al. "High-Quality and Low Dielectric Constant SiO2 CVD Using High Density Plasma", Dry Processing Symposium. Vol. 2. November 1993. pp. 163-168.					
<u>JK</u> CC	Musaka, "Single Step Gap Filling Technology fo Subhalf Micron Metal Spacings on Plasma Enhanced TEOS/O2 Chemical Vapor Deposition System", International Conference on Solid State Devices and Materials. Japan. 1993. pp. 510-512.					
<u>JK</u> CD	Galiano et al. "Stress-Temperature Behavior of Oxide Films Used for Intermetal Dielectric Applications", VMIC Conference. June 1992. pp. 100-106.					
<u>JK</u> CE	Yu et al. "Step Coverage Study of Peteos Deposition for Intermetal Dielectric Applications", VMIC Conference. June 1990. pp. 166-172.					
<u>JK</u> CF	Chang et al. "Frequency Effects and Properties of Plasma Deposited Fluorinated Silicon Nitride", American Vacuum Society. 1988. pp. 524-532.					
<u>JK</u> CG	Robles et al. "Effects of RF Frequency and Deposition Rates on the Moisture Resistance of PECVD TEOS-Based Oxide Films", ECS Extended Abstracts. Vol. 92-1. May 1992. pp.215-216.					
EXAMINER			DATE CONSIDERED			

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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.